

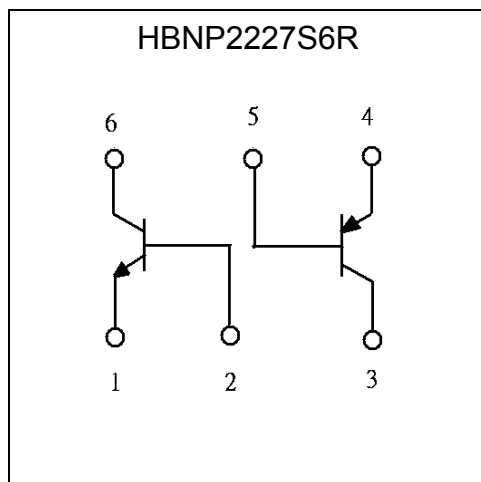
**General Purpose NPN / PNP Epitaxial Planar Transistors
 (dual transistors)**

HBNP2227S6R

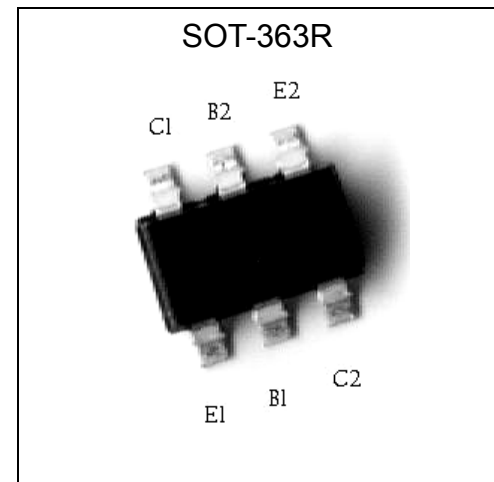
Features

- Includes a PN2222A chip and PN2907A chip in a SOT-363R package.
- Mounting possible with SOT-323 automatic mounting machines.
- Transistor elements are independent, eliminating interference.
- Mounting cost and area can be cut in half.
- Pb-free lead plating package.

Equivalent Circuit

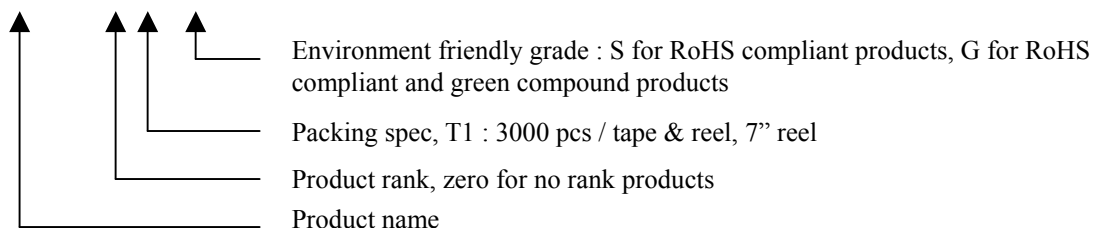


Outline



Ordering Information

Device	Package	Shipping
HBNP2227S6R-0-T1-G	SOT-363 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel



**Absolute Maximum Ratings** (Ta=25°C)

Parameter	Symbol	Limits		Unit
		TR1 (NPN)	TR2 (PNP)	
Collector-Base Voltage	V _{CBO}	75	-60	V
Collector-Emitter Voltage	V _{CEO}	40	-60	V
Emitter-Base Voltage	V _{EBO}	6	-5	V
Collector Current	I _C	600	-600	mA
Power Dissipation	P _d	200(total) *1		mW
Junction Temperature	T _j	150		°C
Storage Temperature	T _{stg}	-55~+150		°C

Note: *1 150mW per element must not be exceeded.

Characteristics (Ta=25°C)• **TR1 (NPN)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	75	-	-	V	I _C =10μA
BV _{CEO}	40	-	-	V	I _C =10mA
BV _{EBO}	6	-	-	V	I _E =10μA
I _{CBO}	-	-	10	nA	V _{CB} =60V
I _{CEX}	-	-	10	nA	V _{CE} =60V, V _{EB} =3V
I _{EBO}	-	-	10	nA	V _{EB} =3V
*V _{CE(sat)}	-	-	0.3	V	I _C =150mA, I _B =15mA
*V _{CE(sat)}	-	-	1.0	V	I _C =500mA, I _B =50mA
*V _{BE(sat)}	0.6	-	1.2	V	I _C =150mA, I _B =15mA
*V _{BE(sat)}	-	-	2.0	V	I _C =500mA, I _B =50mA
h _{FE}	35	-	-	-	V _{CE} =10V, I _C =100μA
h _{FE}	50	-	-	-	V _{CE} =10V, I _C =1mA
h _{FE}	75	-	-	-	V _{CE} =10V, I _C =10mA
*h _{FE}	100	-	300	-	V _{CE} =10V, I _C =150mA
*h _{FE}	35	-	-	-	V _{CE} =1V, I _C =150mA
*h _{FE}	40	-	-	-	V _{CE} =10V, I _C =500mA
f _T	300	-	-	MHz	V _{CE} =20V, I _C =20mA, f=100MHz
C _{ob}	-	-	8	pF	V _{CB} =10V, f=1MHz

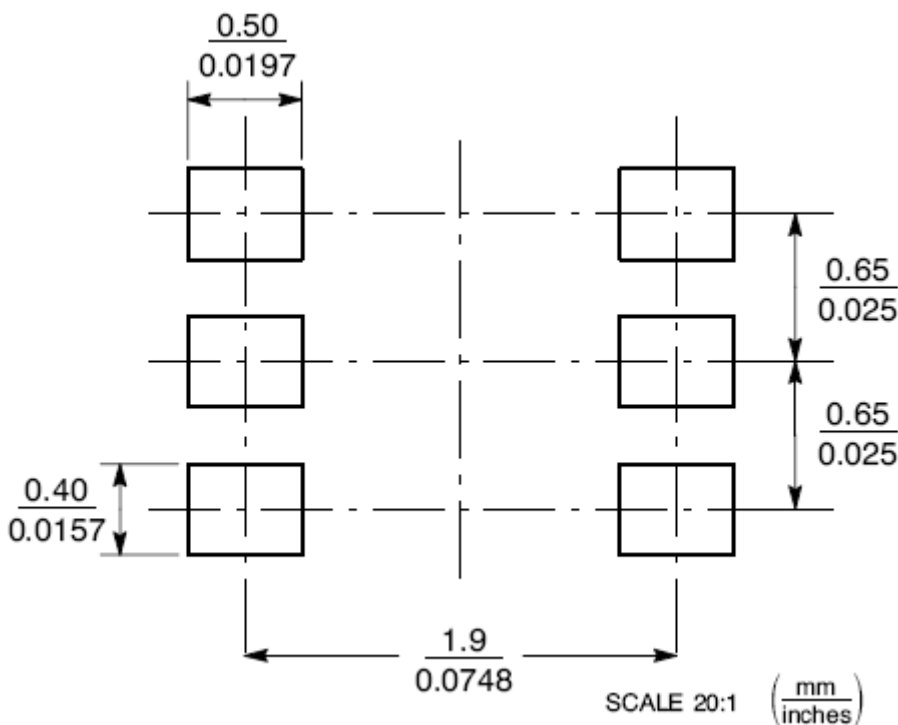
*Pulse Test: Pulse Width ≤380μs, Duty Cycle ≤2%

• **TR2 (PNP)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	-60	-	-	V	I _C =-10μA
BV _{CEO}	-60	-	-	V	I _C =-10mA
BV _{EB0}	-5	-	-	V	I _E =-10μA
I _{CBO}	-	-	-10	nA	V _{CB} =-50V
I _{CEX}	-	-	-50	nA	V _{CE} =-30V, V _{EB} =-0.5V
I _{EB0}	-	-	-10	nA	V _{EB} =-3V
*V _{CE(sat)}	-	-	-0.4	V	I _C =-150mA, I _B =-15mA
*V _{CE(sat)}	-	-	-1.6	V	I _C =-500mA, I _B =-50mA
*V _{BE(sat)}	-	-	-1.3	V	I _C =-150mA, I _B =-15mA
*V _{BE(sat)}	-	-	-2.6	V	I _C =-500mA, I _B =-50mA
h _{FE}	75	-	-	-	V _{CE} =-10V, I _C =-100μA
h _{FE}	100	-	-	-	V _{CE} =-10V, I _C =-1mA
h _{FE}	100	-	-	-	V _{CE} =-10V, I _C =-10mA
*h _{FE}	100	-	300	-	V _{CE} =-10V, I _C =-150mA
*h _{FE}	50	-	-	-	V _{CE} =-10V, I _C =-500mA
f _T	200	-	-	MHz	V _{CE} =-20V, I _C =-50mA, f=100MHz
C _{ob}	-	-	8	pF	V _{CB} =-10V, f=1MHz

*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

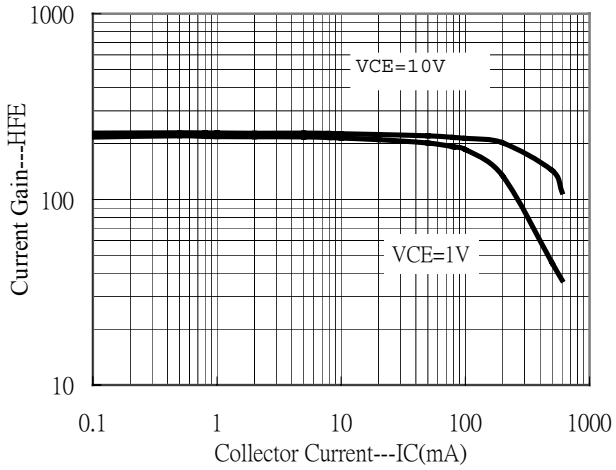
Recommended Soldering Footprint



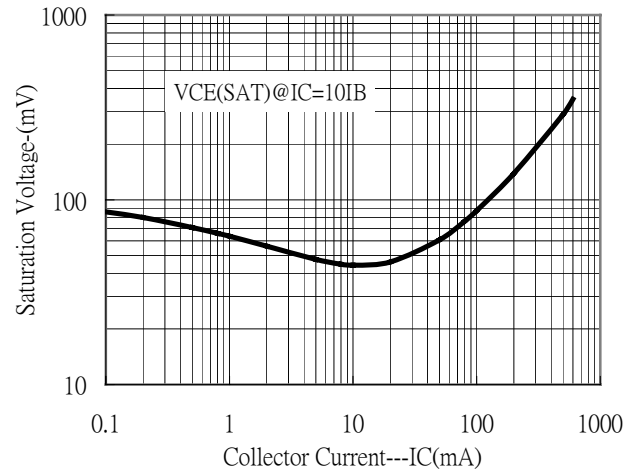
Typical Characteristics

- TR1 (NPN)

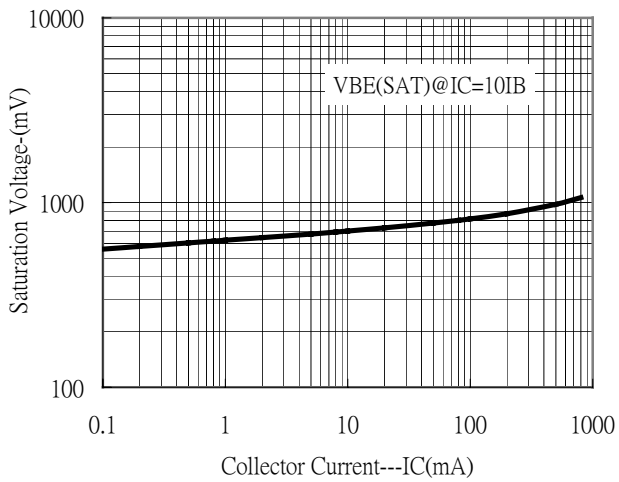
Current Gain vs Collector Current



Saturation Voltage vs Collector Current



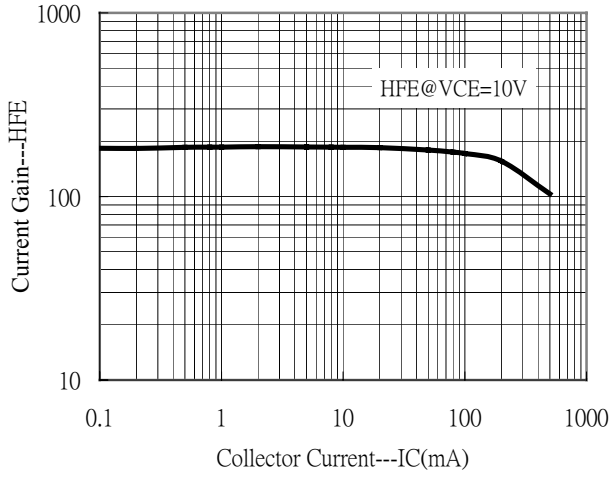
Saturation Voltage vs Collector Current



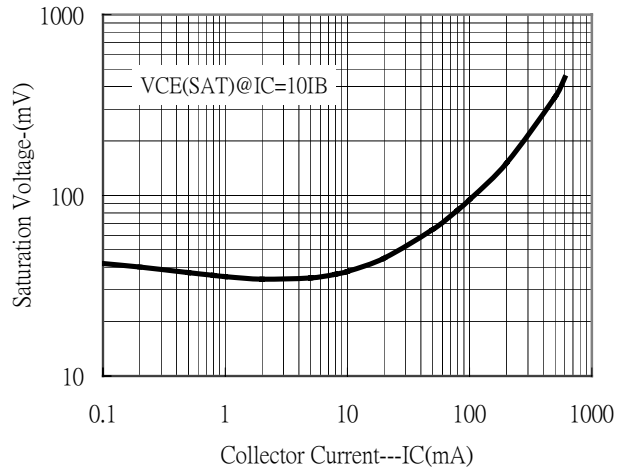


• TR2 (PNP)

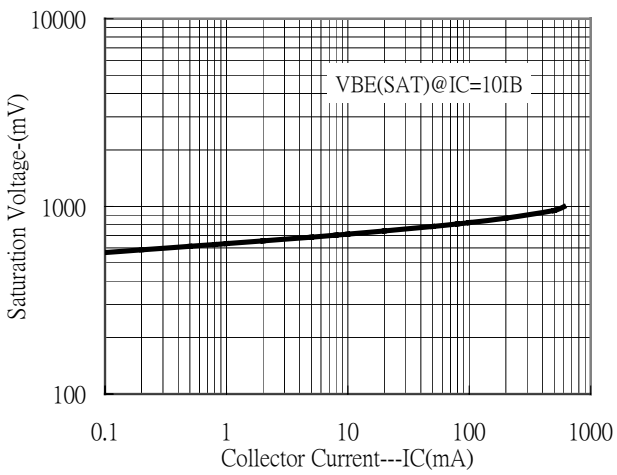
Current Gain vs Collector Current



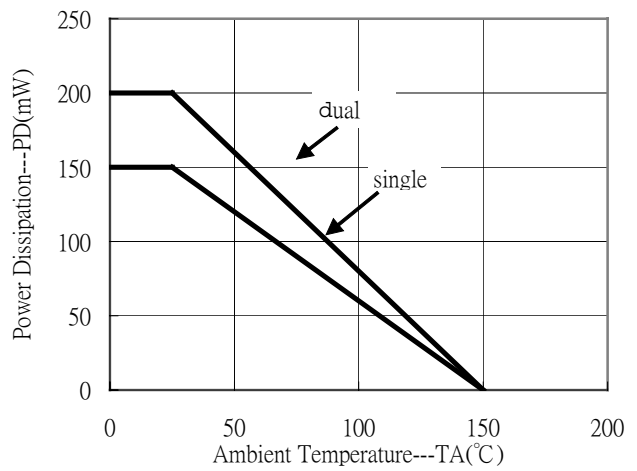
Saturation Voltage vs Collector Current

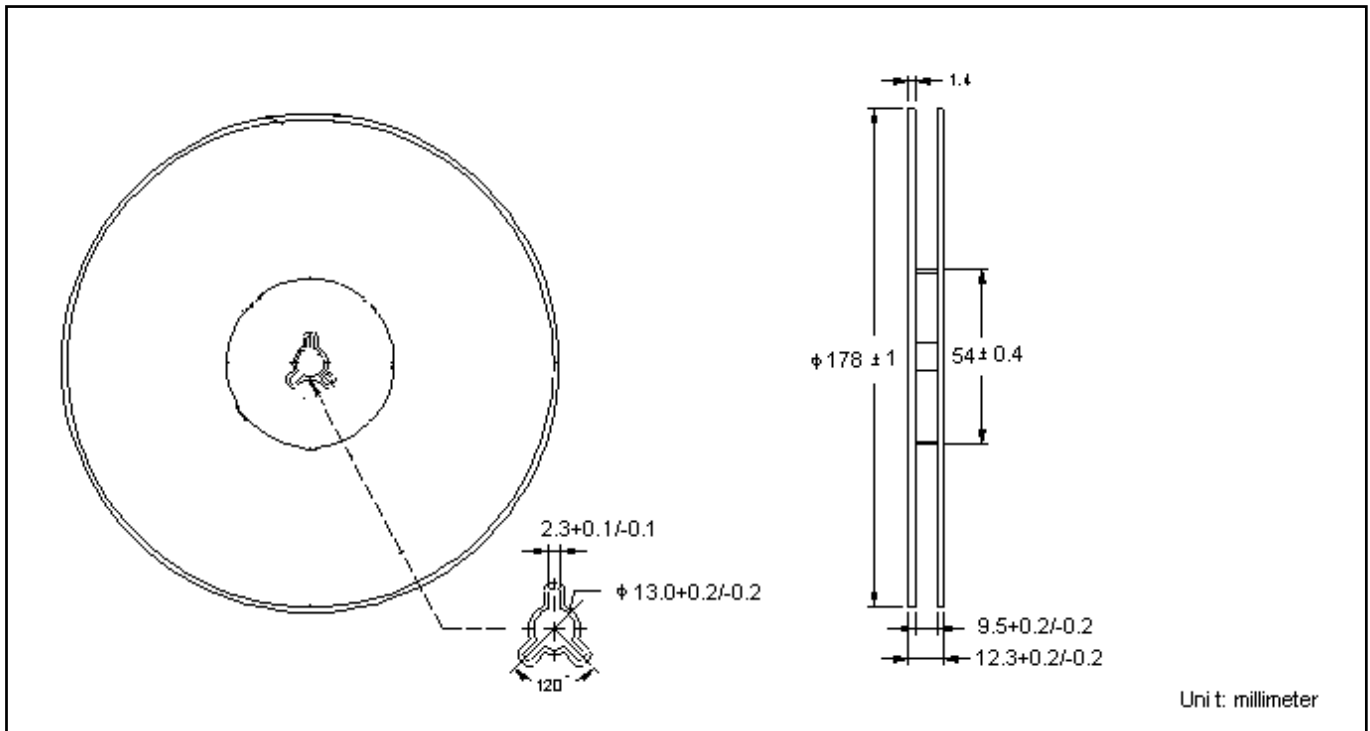
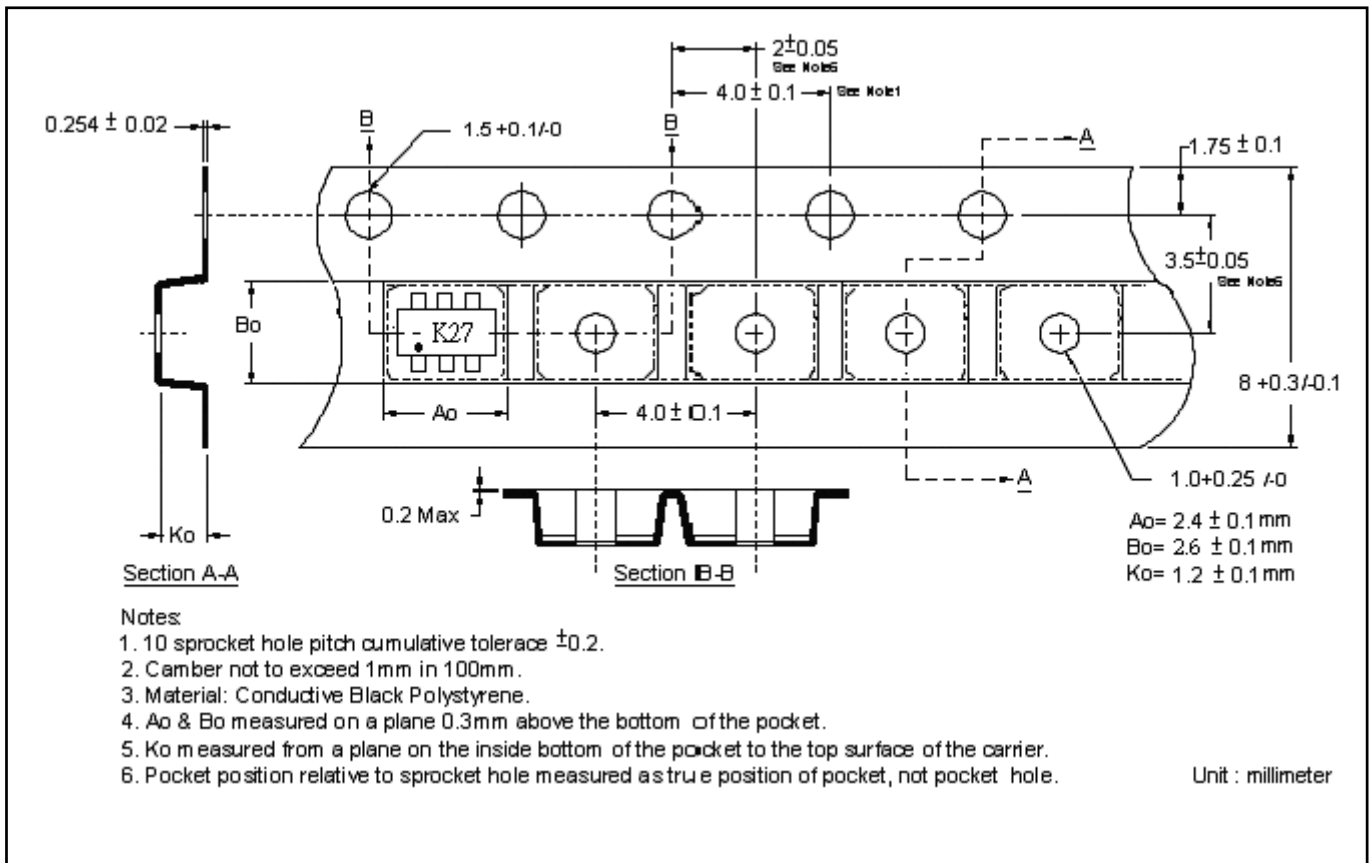


Saturation Voltage & Collector Current



Power Derating Curves

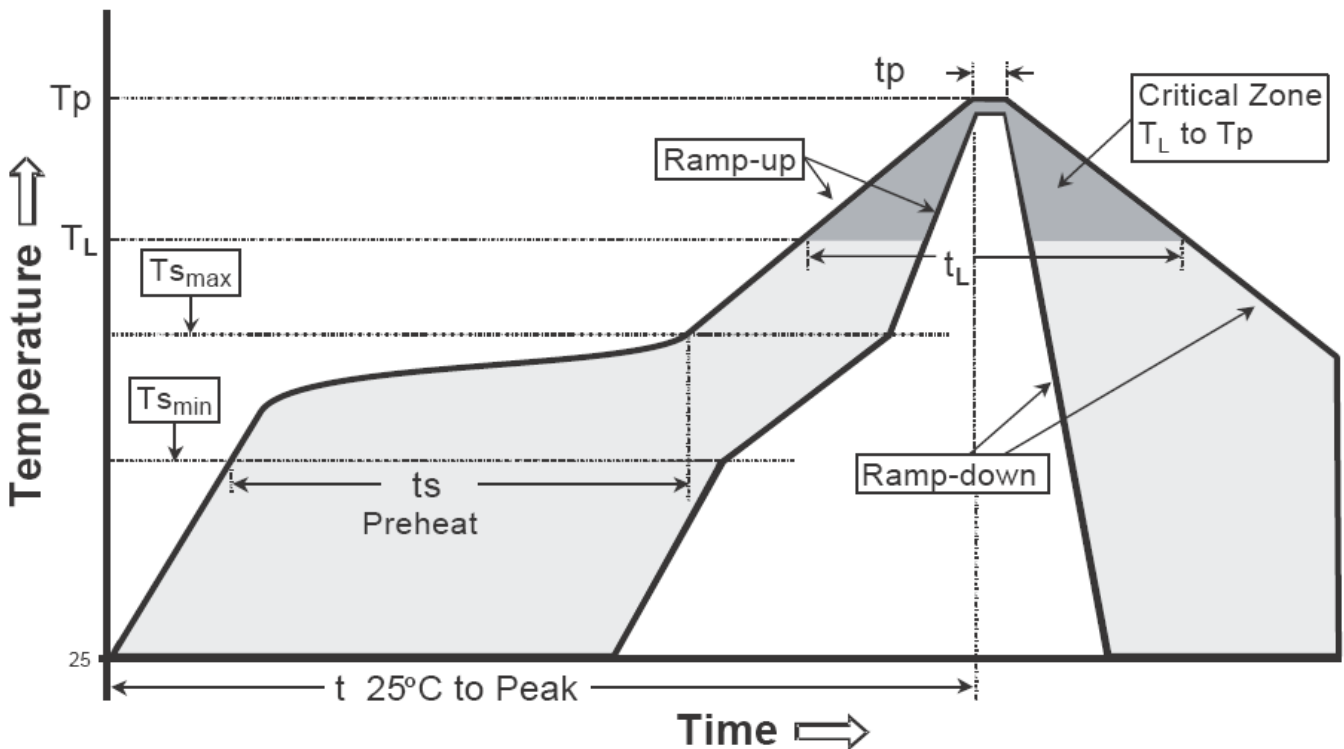


Reel Dimension**Carrier Tape Dimension**

Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

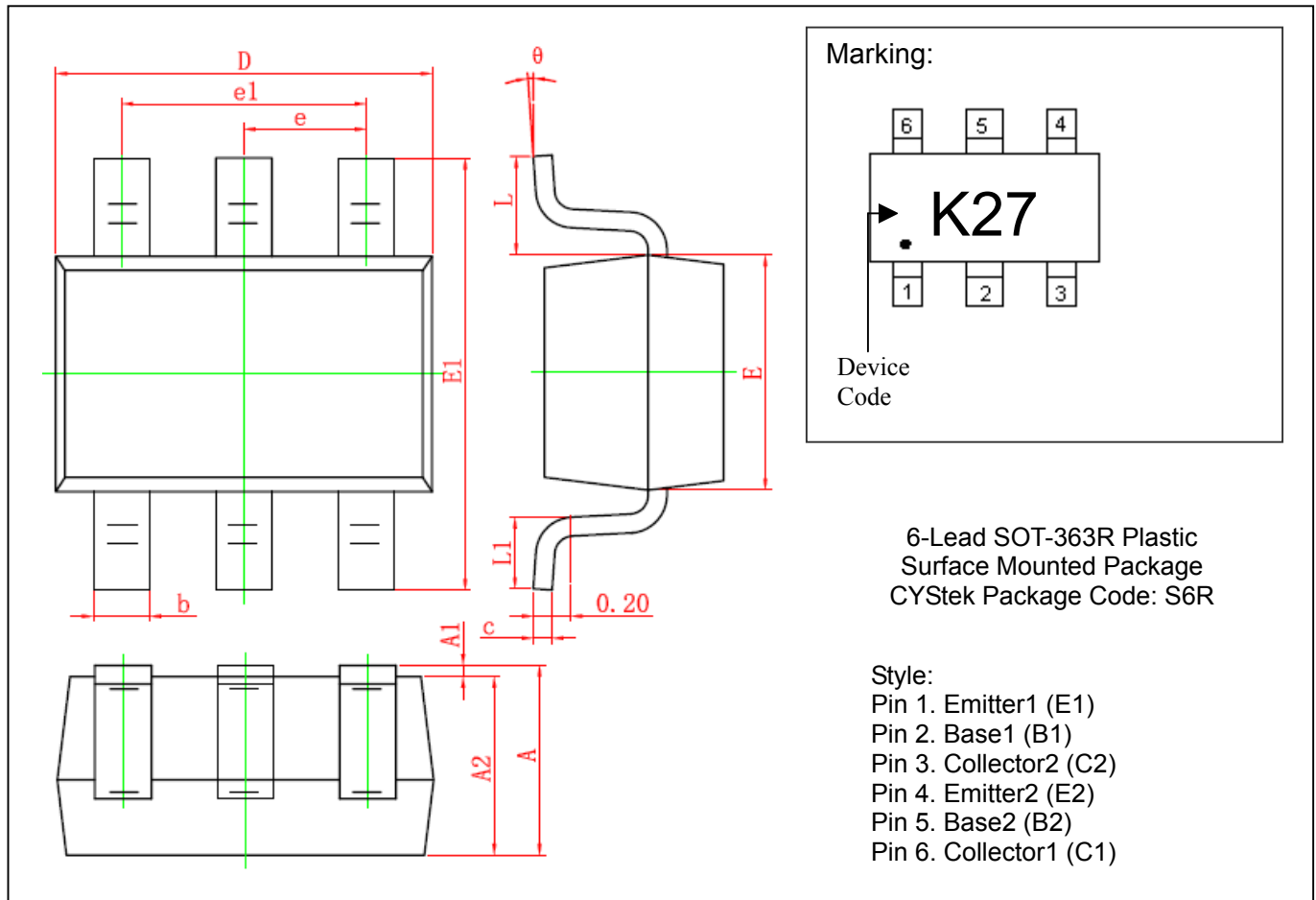
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-363 Dimension



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043	E1	2.150	2.450	0.085	0.096
A1	0.000	0.100	0.000	0.004	e	0.650 TYP		0.026 TYP	
A2	0.900	1.000	0.035	0.039	e1	1.200	1.400	0.047	0.055
b	0.150	0.350	0.006	0.014	L	0.525 REF		0.021 REF	
c	0.080	0.150	0.003	0.006	L1	0.260	0.460	0.010	0.018
D	2.000	2.200	0.079	0.087	θ	0°	8°	0°	8°
E	1.150	1.350	0.045	0.053					

Notes : 1.Controlling dimension : millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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